



## Synchronous Rectifier Controller

Preliminary Specifications Subject to Change without Notice

#### **DESCRIPTION**

JW®7726B is a synchronous rectifier controller, used for the secondary side rectification of isolation topologies, such as Active Clamp Flyback and CCM/QR/DCM Flyback. By driving an external MOSFET, JW7726B is able to significantly improve the efficiency comparing with the conventional diode rectifier.

When JW7726B senses  $V_{ds}$  of MOSFET less than -140mV, it turns on the MOSFET. Once the  $V_{ds}$  is greater than -3mV, JW7726B turns off the MOSFET.

JW7726B supports multiple operation modes, such as DCM, CrCM, CCM and Quasi-Resonant. By implementing the Joulwatt proprietary technology, JW7726B is able to handle CCM operation.

JW7726B is available in SOT23-6 package.

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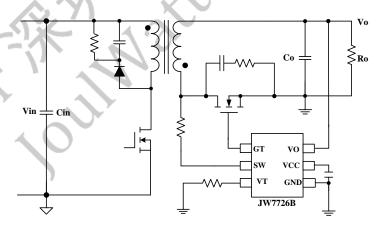
## **FEATURES**

- Supports Active Clamp Flyback, DCM, Quasi-Resonant, and CCM Flyback
- Support High-side and Low-side Rectification
- Output Voltage Directly Supply VCC
- Low Quiescent Current
- Fast Driver Capability for CCM Operation
- SOT23-6 Package

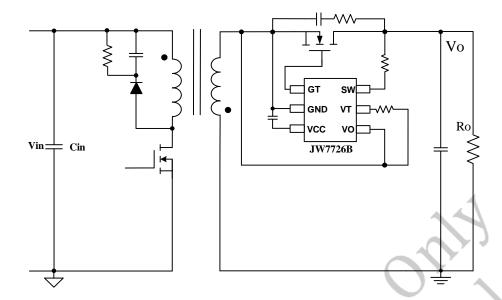
## **APPLICATIONS**

- Active Clamp Flyback and Flyback Converters
- Adaptor
- LCD and PDP TV

# **TYPICAL APPLICATION**



JW7726B Typical Application for Low-side.

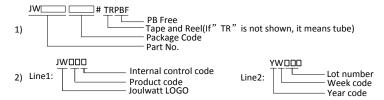


JW7726B Typical Application for High-side.

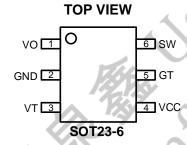
## **ORDER INFORMATION**

DEVICE <sup>1)</sup>	PACKAGE	TOP MARKING <sup>2)</sup>
JW7726BSOTB#TRPBF	SOT23-6	JWEW □ YW □ □ □

#### Notes:



# **PIN CONFIGURATION**



# ABSOLUTE MAXIMUM RATING1)

7.2002012 0				
SW PIN				
VO PIN	0.3 to 28V			
VCC, GT PIN				
VT PIN				
Junction Temperature <sup>2) 3)</sup>	150°C			
Lead Temperature	260°C			
Storage Temperature	65°C to150°C			
Continuous Power Dissipation(T <sub>A</sub> =+25°C) <sup>4)</sup> SOT23-6	0.56W			
ESD Susceptibility (Human Body Model)	2kV			
RECOMMENDED OPERATING CONDITIONS				
SW Pin	4.7V to 120V			
VO Pin	4.7V to 25V			
VCC, GT PIN	4V to 8.5V			
Operation Junction Temperature(T <sub>J</sub> )	-40°C to 125°C			
THERMAL PERFORMANCE <sup>5)</sup>	$ heta_{\!\scriptscriptstyle J\!A} \qquad  heta_{\!\scriptscriptstyle J\!c}$			
SOT23-6				

#### Note:

1) Exceeding these ratings may damage the device. These stress rating do not imply function operation of the device at any other conditions beyond those indicated under RECOMMENDED OPERATING CONDITIONS.

- 2) Continuous operation over the specified absolute maximum operating junction temperature may damage the device.
- 3) The device is not guaranteed to function outside of its operating conditions.
- 4) The maximum allowable continuous power dissipation at any ambient temperature is calculated by  $P_D(MAX)=(T_J(MAX)-T_A)/\theta_{JA}$ .
- 5) Measured on JESD51-7, 4-layer PCB.



## **ELECTRICAL CHARACTERISTICS**

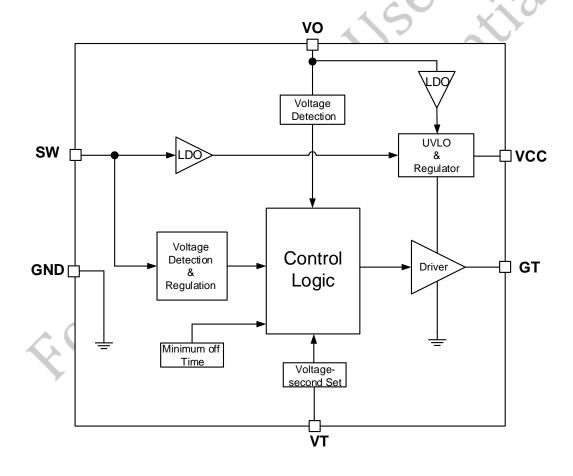
TA = 25°C, unless otherwise stated								
Item	Symbol	Condition	Min.	Тур.	Max.	Units		
VCC Section								
VCC Voltage	VCC	SW=40V, VCC=2.2uF	7.5	8	8.5	V		
VCC Startup Voltage	VCC_Startup		4.2	4.5	4.8	V		
VCC UVLO	Vcc_uvlo		3.8	3.95	4.1	V		
Operation Current (GT On)	Ivcc	GT=5nF,VCC=2.2uF	0.7	0.9	1.1	mA		
Quiescent Current	Iq	VCC=4.5V, VCC=2.2uF	95	110	125	uA		
Gate Section								
Gate Turn On Threshold	V <sub>MOS_ON</sub>		-162	-140	-116	mV		
Gate Turn Off Threshold	V <sub>MOS_OFF</sub>	, (	-15	-3	10	mV		
Gate Turn On Voltage	$V_{GT}$	SW=32V, VCC=2.2uF	V <sub>CC</sub> -1	V <sub>CC</sub>		V		
Maximum Gate Pull Up Current 6)	lgu			0.6		Α		
Maximum Gate Pull Down Current 6)	I <sub>GD</sub>	1/2/1/20		4		Α		
Gate Minimum On Time	T <sub>MIN</sub> ON	VA TOY CA	520	560	600	ns		
Absolutely Minimum Off Time	T <sub>MIN_OFF</sub>		280	330	380	ns		
Turn-on Total Delay 6)	T <sub>DON</sub>	C <sub>LOAD</sub> =4.7nF		50		ns		
Turn-off Total Delay 6)	TDOF	C <sub>LOAD</sub> =4.7nF		20		ns		
SW and VO Section	SW and VO Section							
VCC Charge Current	I <sub>SW_CHG</sub>	SW=40V, VCC=6V	75	85		mA		
SW Regulation Voltage	V <sub>MOS_REG</sub>	2	-50	-40	-20	mV		
SW Control Voltage MAX	VMOS_REG_	)	-185	-160	-145	mV		
VO Enable Charge Voltage	Vo_en	VCC=4V, SW=0V, rising	4.5	4.6	4.7	V		
VO Disable Charge Voltage	Vo_dis	VCC=4V, SW=0V, falling	4.4	4.5	4.6	V		
VO Charge Current	Ivo_снg	SW=0V, VCC=6V, VO=12V	30	40		mA		

<sup>6)</sup> Guaranteed by design.

## **PIN DESCRIPTION**

Part No. SOT23-6	Name	Description	
1	VO	Output voltage sensing and charging to VCC.	
2	GND	Ground.	
3	VT	Set the voltage-second product.	
4	VCC	Power supply. Bypass a capacitor between VCC and GND.	
5	GT	Drive the external MOSFET.	
6	SW	External power MOSFET drain voltage sensing. Charging to VCC.	

## **BLOCK DIAGRAM**



#### **FUNCTIONAL DESCRIPTION**

#### Operation

JW7726B is a synchronous rectifier controller which combined with external MOSFET can replace the Schottky Barrier Diode. It supports all operations, such as DCM, CrCM, (Quasi-Resonant) and CCM when adopted in Active Clamp Flyback and Flyback converters.

### **Startup**

During the startup period, when the VCC is charged up by the two internal LDOs connected to SW and VO pin respectively.

When VO is lower than 4.5V (falling), JW7726B can power itself through the internal LDO connected to SW pin during the SR turn-off period, which means primary the primary side MOSFET is turned on and SW presents a positive voltage. A capacitor between VCC and GND is required to store the energy and supply to IC during the SR turn-on period.

When VO is above 4.6V (rising), the VO pin charges VCC pin.

Once the VCC voltage exceeds  $V_{CC\_Startup}$ , the JW7726B exits the UVLO. If VCC is lower than  $V_{CC\_UVLO}$ , the external MOSFET is turned off. The current flows though body diode before the VCC reaches to the startup voltage  $V_{CC\_Startup}$ .

### **Under-Voltage Lockout (UVLO)**

When the VCC is below UVLO threshold, the external MOSFET is turned off and pulled low internally. Once the VCC exceeds the startup voltage Vcc\_startup, the parts is activated again.

#### **Turn On Phase**

There are two conditions for the JW7726B to turn on the SR, i.e. Vsw, voltage-second value on SW pin when primary side switch is on, and the turn on phase is shown in Fig. 1.

- 1) Vsw: when the synchronous MOEFET is conducting, current flows through the body diode of MOSFET, which generates a negative voltage  $V_{SW}$  across it. When  $V_{SW}$  is lower than  $V_{MOS\_ON}$ , the part will pull the gate high to turn on the synchronous MOSFET after turn on delay time  $T_{DON}$  if the other condition is met.
- 2) Volt-second of SW: in DCM and QR operation, there are parasitic oscillations. In some applications, the drain resonant voltage may fall below the SR turn on threshold, especially for the first couple rings. SR could be falsely turned on, which may cause shoot through issue and result in high power loss. The volt-second value of SW pin can be used to distinguish the parasitic ring from normal primary side switch on. The threshold can be set by the resistance at VT pin. The curve is shown in Fig. 2.

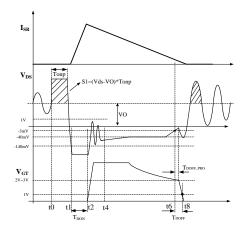


Fig. 1 Turn on delay and turn off delay

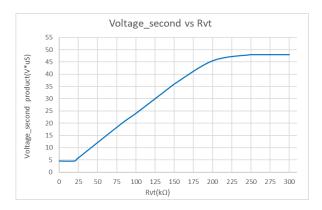


Fig. 2 Volt-second value vs. VT resistance

#### **Minimum On Time (MOT)**

When the synchronous MOSFET is turn on, there is a minimum on time for the SR. The  $V_{SW}$  voltage may have a parasitic ring when the synchronous MOSFET turns on. So, a minimum on time (MOT) is very important to avoid the MOSFET turn off threshold is false triggered. Minimum on time is 560ns for high frequency applications.

## **Conducting Phase**

When the synchronous MOSFET is turned on, the drain source voltage Vsw it is determined by its on resistance and the current through it. The part adjusts the gate voltage and regulates the Vsw to the internal threshold (typical -40mV) after the synchronous MOSFET turn on. When

the  $V_{\text{SW}}$  is lower than -40mV, the gate keeps its maximum voltage. And the synchronous MOSFET is fully on.

The Vsw rises when the current follow through the MOSFET decreases. The gate voltage will be decreased to increase its on resistance and regulate the Vsw around -40mV.

It should be noted that the typical regulation threshold (-40mV) during MOSFET on time is not fixed, it can be internally changed to ensure the proper operation under CCM mode.

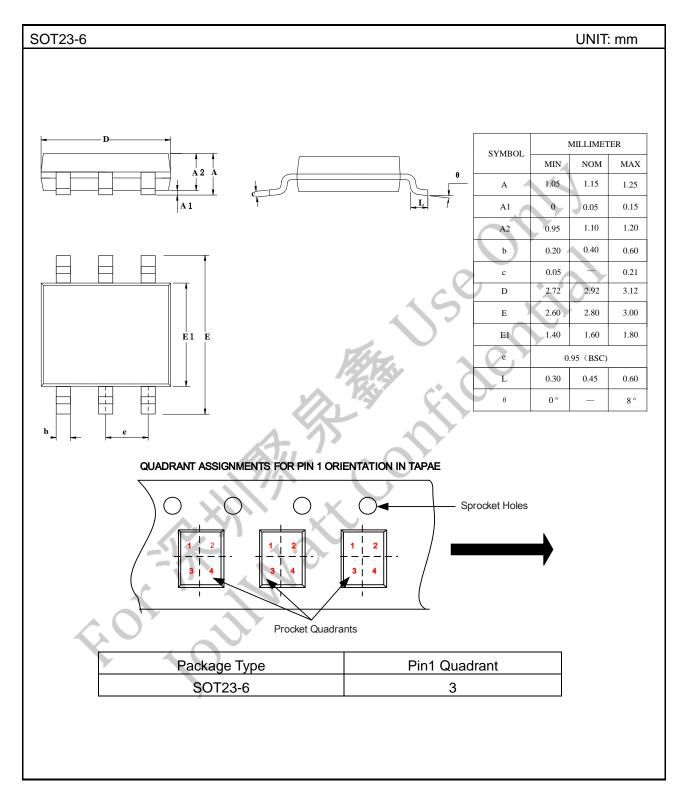
#### **Turn Off Phase**

After synchronous MOSFET conducting, once the voltage VSW touches the MOSFET turn off threshold (-3mV), the gate is pulled to low after a turn off delay time TDOFF. A 330nS blanking time is necessary to avoid error trigger. The banking time is reset once Vsw rises above 2.5V.

#### **Output Voltage Detection**

The JW7726B has output voltage detection function via VO pin. VCC is charged from VO pin when VO is higher than 4.6V to save power loss caused by the LDO when charging from SW pin to VCC pin. When VO drops below 4.5V, the JW7726B is powered from SW pin.

## **PACKAGE OUTLINE**



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